

Title (en)
Method and apparatus for terahertz imaging

Title (de)
Verfahren und Vorrichtung zur Abbildung im Terahertzbereich

Title (fr)
Procédé et dispositif pour l'imagerie dans les gammes térahertz

Publication
EP 0727671 A3 19970305 (EN)

Application
EP 96300828 A 19960207

Priority
US 38893395 A 19950215

Abstract (en)
[origin: EP0727671A2] Certain material and objects can be characterized by a frequency-dependent absorption, dispersion, and reflection of terahertz transients in signals which pass illuminate the material or object. The present terahertz imaging system analyses that frequency dependence in the time-domain by collecting that transmitted signal propagating through the object and then processing the information contained in those signals for every point or "pixel" on that object. This is a non-invasive imaging technique that is capable of differentiating between different materials, chemical compositions, or environments. <IMAGE>

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G01R 31/265; **G01N 21/35**

IPC 8 full level
G01J 3/28 (2006.01); **G01N 21/17** (2006.01); **G01N 21/27** (2006.01); **G01N 21/35** (2006.01); **G01N 21/49** (2006.01); **G01R 31/308** (2006.01)

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G01N 21/3563 (2013.01 - EP US); **G01N 21/3586** (2013.01 - EP US); **G01N 21/49** (2013.01 - EP US); **G01R 31/308** (2013.01 - EP US)

Citation (search report)
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